

# 2N5322 Transistors

## Si PNP Power BJT

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Military/High-Rel N

$V_{(BR)CEO}$  (V) 75

$V_{(BR)CBO}$  (V) 100

$I_C$  Max. (A) 2.0

Absolute Max. Power Diss. (W) 10

Maximum Operating Temp ( $\theta C$ ) 175 $\bar{o}$

$I_{CBO}$  Max. (A) 100 $\mu$

@ $V_{CBO}$  (V) (Test Condition)

$V_{CEsat}$  Max. (V)

@ $I_C$  (A) (Test Condition)

@ $I_B$  (A) (Test Condition)

$h_{FE}$  Min. Current gain. 30

$h_{FE}$  Max. Current gain. 130

@ $I_C$  (A) (Test Condition) 500m

@ $V_{CE}$  (V) (Test Condition) 4.0

$f_T$  Min. (Hz) Transition Freq 50M

@ $I_C$  (A) (Test Condition)

@ $V_{CE}$  (V) (Test Condition)

$t_d$  Max. (s) Delay time.

$t_r$  Max. (s) Rise time

$t_{on}$  Max. (s) On time. 100n